



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: IKEMASU et al.

Serial Number: 10 050,169

Filed: January 18, 2002

Prior Group Art Unit: 2814

For: HIGHLY INTEGRATED AND RELIABLE DRAM
AND ITS MANUFACTURE

Prior Examiner: WEISS

Commissioner for Patents
Washington, D.C. 20231

February 27, 2002

Sir:

Transmitted herewith is an Amendment in the above-identified application.

The fee has been calculated as shown below:

		CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid For	=	Present Extra	Small Entity	Large Entity	Additional Fee
Total Claims	37	23	=	14	X \$9	X \$18	\$252.00
Independent Claims	3	0	=	0	X \$42	X \$84	0
# First Presentation of Multiple Dependent Claims					\$140	280	
						TOTAL FEES ENCLOSED:	\$252.00

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X Enclosed please find our check in the amount of **\$252.00** for the additional claims fee in connection with this amendment. The Commissioner is hereby authorized to charge payment for any additional fees associated with this communication or credit any overpayment to Deposit Account No. 01-2340. Two duplicates of this sheet are attached.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP



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PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

February 27, 2002

Sir:

Prior to examination of the above-identified divisional application, please amend the same as follows:

IN THE CLAIMS:

Please amend Claim 1, as follows:

1. (Amended) A semiconductor device comprising:
 - a semiconductor substrate;
 - a first insulating film formed over said semiconductor substrate;
 - a capacitor formed over said first insulating film, and having one electrode which includes an extension extending over said first insulating film;
 - a second insulating film formed over said first insulating film;
 - a first contact hole formed through said second insulating film and said extension of the one electrode; and
 - a first conductor pattern burying said first contact hole.